

## INFORMATION DISCLOSURE

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Applicant(s): OOI et al.

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## U.S. PATENTS

Patent Number	Issue Date	Name	Class	Sub-class	Filing date
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## FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a
	WO 96/27226	9/06/96	PCT	National Research Council of Canada	n/a
	EP 0812485 B1	12/17/97	Europe	National Research Council Canada	n/a
	EP 0731387 A2	9/11/96	Europe	Samsung Electronics Co., Ltd.	n/a

## OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)

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	"Plasma Immersion AR+ ION Implantation Induced Disorder in Strained InGaAsP Multiple Quantum Wells", Lam et al., 1998, Electronics Letters, GB, IEE Stevenage, vol. 34, no. 8, pages 817-818.
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Examiner's Signature:

Date Considered: 9/21/02

Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered.

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